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**Amendments to the Claims**

Please cancel claims 1-11.

Please add new claims 12-22 as shown below.

**Listing of Claims**

This listing of claims will replace all prior versions and listings of claims in the application:

Claims 1-11 (Cancelled)

12. (New) A method for fabricating finely patterned interconnects having low electrical resistance, the method comprising:

- (a) forming a finely patterned metal-containing interconnect having a first grain size on a carrier material; and
- (b) producing and moving a locally delimited thermal region in the finely patterned metal-interconnect in such a way that a recrystallization of the interconnect is carried out for the purpose of producing an interconnect having a second grain size, the second grain size being enlarged with respect to the first grain size.

13. (New) The method of claim 12 wherein the finely patterned interconnect has feature sized of less than 0.2  $\mu\text{m}$ .

14. (New) The method of claim 12 wherein,  
in act (a), the interconnect is formed in a primary direction and/or in a secondary direction which is substantially perpendicular to the primary direction; and  
in act (b), the movement of the thermal region is carried out substantially in the primary direction and/or in the secondary direction or at an angle of 45 degrees to the primary direction and the second direction.

15. (New) The method of claim 12 wherein act (b) is carried out repeatedly.
16. (New) The method of claim 12 wherein, in act (b), the locally delimited thermal region is produced by means of a fanned-out laser beam, a hot gas, a multiplicity of heating lamps and/or a heating wire.
17. (New) The method of claim 12 wherein the locally delimited thermal region is formed in strip-type or point-type fashion.
18. (New) The method of claim 12 wherein, in act (a), the interconnect has a metal alloy or a doped metal with an impurity proportion of less than 5%.
19. (New) The method of claim 12 wherein the carrier material has a diffusion barrier layer and/or a seed layer.
20. (New) The method of claim 12 wherein, in act (a), a damascene method is carried out.
21. (New) The method of claim 12, wherein the locally delimited thermal region has a temperature of 150 degrees Celsius to 450 degrees Celsius.
22. (New) The method of claim 12 wherein the recrystallization is carried out in a protective gas atmosphere.